

isc Silicon PNP Power Transistor

2SA740

DESCRIPTION

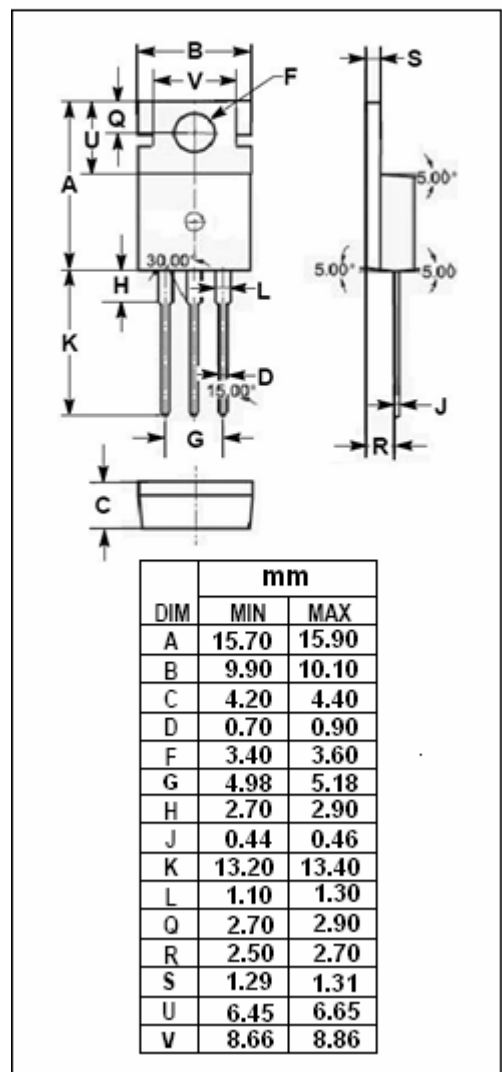
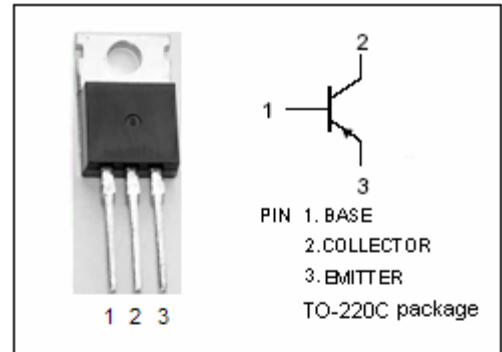
- Collector-Emitter Breakdown Voltage
: $V_{(BR)CEO} = -150V(\text{Min})$
- DC Current Gain
: $h_{FE} = 40-140 @ I_C = -0.5A$
- Complement to Type 2SC1448

APPLICATIONS

- Power amplifier applications.
- Vertical output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_E	Emitter Current-Continuous	1.5	A
P_C	Total Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	W
	Total Power Dissipation @ $T_C=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor

2SA740

ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -5\text{mA}$; $I_B = 0$	-150			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1\text{mA}$; $I_E = 0$	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}$; $I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}$; $I_B = -50\text{mA}$			-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -0.5\text{A}$; $V_{CE} = -10\text{V}$			-1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -100\text{V}$; $I_E = 0$			-20	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$			-10	μA
h_{FE}	DC Current Gain	$I_C = -0.5\text{A}$; $V_{CE} = -10\text{V}$	40		140	
C_{OB}	Output Capacitance	$I_E = 0$; $V_{CB} = -10\text{V}$; $f_{test} = 1\text{MHz}$		90		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}$; $V_{CE} = -10\text{V}$		8		MHz